

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	37	((WOLFGANG) near2 (CLEMENS)).INV.	US-PGPUB; USPAT	ADJ	ON	2007/11/21 08:43
S2	2	((DIETMAR) near2 (ZIPPERER)).INV.	US-PGPUB; USPAT	ADJ	ON	2007/11/21 08:43
S3	551	361/523.ccls.	US-PGPUB; USPAT	ADJ	ON	2007/11/21 08:44
S4	27204	capacitor and insulator and semiconductor and electrode	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2008/05/08 14:41
S6	1667	capacitor.ab. and insulator and semiconductor and electrode and organic	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2008/05/08 14:41
S7	132	capacitor.ab. and insulator and semiconductor and electrode and organic and structured	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2008/05/08 14:42
S8	2	("3512052").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2008/05/08 14:51
S9	9	("3512052").URPN.	USPAT	ADJ	ON	2008/05/08 14:51
S10	89	("20020022284" "20020025391" "20020053320" "20020056839" "20020068392" "20020130042" "20020167003" "20020170897" "20020195644" "20030059987" "20030112576" "20030175427" "20040002176" "20040013982" "20040026689" "20040084670" "20040211329" "3512052" "3769096" "3955098" "4302648" "4340657" "4442019" "4865197" "4937119" "5173835" "5206525" "5259926" "5321240" "5347144" "5364735" "5395504" "5480839" "5486851" "5502396"	US-PGPUB; USPAT; USOCR	ADJ	ON	2008/05/08 14:54

		"5546889" "5569879" "5574291" "5578513" "5580794" "5625199" "5630986" "5652645" "5691089" "5705826" "5729428" "5854139" "5869972" "5883397" "5892244" "5967048" "5970318" "5973598" "5994773" "5997817" "5998805" "6036919" "6045977" "6072716" "6083104" "6087196" "6133835" "6150668" "6197663" "6207472" "6215130" "6221553" "6251513" "6284562" "6300141" "6321571" "6322736" "6329226" "6330464" "6335539" "6340822" "6344662" "6362509" "6384804" "6403396" "6429450" "6498114" "6517995" "6555840" "6593690" "6603139" "6621098" "6852583").PN. OR ("7064345").URPN.				
S11	57	("5347144" "5355235"). PN. OR ("5705826").URPN.	US-PGPUB; USPAT; USOCR	ADJ	ON	2008/05/08 14:58
S12	70	capacitor.ab. and insulator layer and semiconductor layer and electrode and organic	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2008/05/08 16:06
S13	13733	FET and capacitor same source same drain	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2008/05/14 13:29
S14	4685	FET and electrode and semiconductor and p near type and n near type and insulator and voltage	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2008/05/14 13:29
S15	2215	FET and structure with electrode and semiconductor and p near type and n near type and insulator and voltage	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2008/05/14 13:31
S16	882	FET and structure with electrode and semiconductor and p near type and n near type and insulator and voltage and capacitor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2008/05/14 13:31

S17	122	FET and structure with electrode and semiconductor and p near type and n near type and insulator and voltage and capacitor and organic with substrate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2008/05/14 13:34
S18	1758	FET and electrode and semiconductor and p near type and n near type and insulator and voltage and first with semiconductor with layer and second with semiconductor with layer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2008/05/14 13:39
S19	359	FET and electrode and semiconductor and p near type and n near type and insulator and voltage and first with semiconductor with layer and second with semiconductor with layer and organic	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2008/05/14 14:01
S20	998	FET and electrode and semiconductor and p near type and n near type and insulator and voltage and organic	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2008/05/14 14:03
S21	349	FET and electrode and semiconductor and p near type and n near type and insulator and voltage and organic and source with metal and drain with metal	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2008/05/14 14:05
S23	2862	capacitor and electrode and organic same semiconductor and first with semiconductor and second with semiconductor and (insulator or dielectric)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2008/05/14 14:25
S24	1712	capacitor and electrode and organic with semiconductor and first with semiconductor and second with semiconductor and (insulator or dielectric)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2008/05/14 14:25
S25	9	("3512052").URPN.	USPAT	ADJ	ON	2008/05/14 14:26

S26	1154	capacitor and electrode and organic with semiconductor and first with semiconductor with layer and second with semiconductor with layer and (insulator or dielectric)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2008/05/14 14:29
S27	314	(capacitor.ab. or capacitor.cfm. or capacitor.ti.) and electrode and organic with semiconductor and first with semiconductor with layer and second with semiconductor with layer and (insulator or dielectric)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2008/05/14 14:39
S29	29476	(field effect transistor or capacitor) and (first with semiconductor) same (second with semiconductor) and electrode and (insulator or dielectric)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2008/05/14 14:50
S30	5067	(field effect transistor or capacitor) and (first with semiconductor) same (second with semiconductor) with electrode with (insulator or dielectric)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2008/05/14 14:51
S31	3971	(capacitor) and (first with semiconductor) same (second with semiconductor) with electrode with (insulator or dielectric)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2008/05/14 14:52
S32	311	361/277.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2008/05/14 15:07
S33	470	361/278.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2008/05/14 15:07
S34	223	361/281.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2008/05/14 15:35
S36	1	("5694355").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2008/05/14 16:01
S37	1	("6791402").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2008/05/14 16:02

S38	6666	FET and capacitor same source with drain with connect\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2008/05/15 06:35
S39	7848	capacitor.ab. and insulator and semiconductor and electrode	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2008/05/15 06:39
S40	6666	FET and capacitor same source with drain with connect\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2008/05/15 08:01
S41	1639	FET.ab. and capacitor same source with drain with connect\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2008/05/15 08:03
S42	4791	FET and capacitor same source near5 connect\$4 near5 drain	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2008/05/15 09:04
S43	0	FET and capacitor same source is connected to the drain	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2008/05/15 09:10
S45	460	capacitor and (insulator or dielectric) and (electrode or conductive plate) and (ptype or p near type) and (ntype or n near type) and semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT	ADJ	ON	2008/05/15 11:19
S46	5	("5384649" "5583676"). PN. OR ("6219170").URPN.	US-PGPUB; USPAT; USOCR	ADJ	ON	2008/05/15 11:27
S47	27	capacitor and (insulator or dielectric) and (electrode or conductive plate) and (ptype or p near type) and (ntype or n near type) and semiconductor not silicon	US-PGPUB; USPAT; EPO; JPO; DERWENT	ADJ	ON	2008/05/15 11:32
S48	0	semiconductor near3 insulator near3 semiconductor near3 (electrode or conductor or conductive plate)	US-PGPUB; USPAT; EPO; JPO; DERWENT	ADJ	ON	2008/05/15 11:33
S49	1	semiconductor with insulator with (electrode or conductor or conductive plate)	US-PGPUB; USPAT; EPO; JPO; DERWENT	ADJ	ON	2008/05/15 11:36
S51	44	semiconductor-insulator-semiconductor and capacitor	US-PGPUB; USPAT; EPO; JPO; DERWENT	ADJ	ON	2008/05/15 11:42
S52	1	("5298762").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2008/05/15 11:51

S53	8	semiconductor insulator semiconductor and capacitor and ohmic contact	US-PGPUB; USPAT; EPO; JPO; DERWENT	ADJ	ON	2008/05/15 11:52
S54	325	361/277.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2008/12/03 09:26
S55	480	361/278.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2008/12/03 09:26
S56	227	361/281.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2008/12/03 09:26
S57	459	capacitor.ab,ti. and semiconductor with organic and electrode with (structur\$4 or recess or space)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2008/12/03 09:27
S58	226	capacitor.ab,ti. and semiconductor with organic and electrode with (structur\$4 or recess or space) and (adjust\$4 or vary or vari\$4 or tuning or tun\$4 or control\$4) with (capacitor or capacitance)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2008/12/03 09:30
S59	48	capacitor.ab,ti. and semiconductor with organic and electrode with (structur\$4 or recess or space) and (adjust\$4 or vary or vari\$4 or tuning or tun\$4 or control\$4) with (capacitor or capacitance) and "361".clas.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2008/12/03 09:30
S60	5	361/277-281.ccls. and semiconductor with organic	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2008/12/03 09:34
S61	61	semiconductor with organic and electrode with (structur\$4 or recess or space) and (adjust\$4 or vary or vari\$4 or tuning or tun\$4 or control\$4) with (capacitor or capacitance) and "361".clas.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2008/12/03 09:36
S62	4	((DIETMAR) near2 (ZIPPERER)).INV.	US-PGPUB; USPAT	ADJ	ON	2008/12/03 09:42

S63	41	((WOLFGANG) near2 (CLEMENS)).INV.	US-PGPUB; USPAT	ADJ	ON	2008/12/03 09:42
S64	108	("20020018911" "20020022284" "20020025391" "20020053320" "20020056839" "20020068392" "20020130042" "20020170897" "20020195644" "20030059987" "20030112576" "20030175427" "20040002176" "20040013982" "20040026689" "20040084670" "20040211329" "3512052" "3668483" "3769096" "3939363" "3955098" "4302648" "4340657" "4442019" "4573099" "4598331" "4797773" "4865197" "4910389" "4926052" "4937119" "4977357" "5068634" "5099380" "5142263" "5173835" "5206525" "5259926" "5260848" "5321240" "5347144" "5347185" "5364735" "5395504" "5480839" "5486851" "5502396" "5546889" "5569879" "5574291" "5578513" "5580794" "5625199" "5629530" "5630986" "5652645" "5654863" "5691089" "5705826" "5729428" "5780995" "5854139" "5869972" "5883397" "5892244" "5946551" "5967048" "5970318" "5973598" "5997817" "5998805" "6036919" "6045977" "6060338" "6072716" "6083104" "6087196" "6133835" "6150668" "6197663" "6207472" "6215130" "6221553" "6229180" "6251513" "6284562" "6300141" "6321571" "6322736" "6329226"	US-PGPUB; USPAT; USOCR	ADJ	ON	2008/12/03 09:43

		"6330464" "6335539" "6340822" "6344662" "6362509" "6384804" "6403396" "6429450" "6498114" "6517995" "6555840" "6593690" "6603139" "6621098" "6852583" "6903958"). PN. OR ("7414513").URPN.				
S65	41	((WOLFGANG) near2 (CLEMENS)).INV.	US-PGPUB; USPAT	ADJ	ON	2008/12/08 12:57
S66	4	((DIETMAR) near2 (ZIPPERER)).INV.	US-PGPUB; USPAT	ADJ	ON	2008/12/08 12:57
S67	8	semiconductor insulator semiconductor and capacitor and ohmic contact	US-PGPUB; USPAT; EPO; JPO; DERWENT	ADJ	ON	2008/12/08 13:13
S68	49	capacitor.ab.ti. and semiconductor with organic and electrode with (structur\$4 or recess or space) and (adjust\$4 or vary or vari\$4 or tuning or tun\$4 or control\$4) with (capacitor or capacitance) and "361".clas.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2008/12/08 13:13
S69	87	capacitor.ab.ti. and semiconductor with organic and electrode with (structur\$4 or recess or space) and "361".clas.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2008/12/08 13:17
S70	0	("2007/0030623").URPN.	USPAT	ADJ	ON	2008/12/08 13:20
S71	88	capacitor.ab.ti. and semiconductor with organic and electrode with (area) and "361".clas.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2008/12/08 13:21
S72	1116	capacitor.ab.ti. and (semiconductor near insulator near semiconductor or SIS or S- I-S) and "361".clas.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2008/12/08 13:23
S73	299	capacitor.ab.ti. and (semiconductor near insulator near semiconductor or SIS or S- I-S) and "361".clas. and substrate and electrode with (structur\$4 or recess or space)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2008/12/08 13:23
S74	0	("2006/0098362").URPN.	USPAT	ADJ	ON	2008/12/08 13:30

S75	11	("3512052").URPN.	USPAT	ADJ	ON	2008/12/08 13:30
S76	0	("2004/0223288").URPN.	USPAT	ADJ	ON	2008/12/08 13:33
S77	6	("3307089" "6242989" "6344662" "6380600" "6674116").PN. OR ("6950299").URPN.	US-PGPUB; USPAT; USOCR	ADJ	ON	2008/12/08 13:34
S78	24	capacitor.ab,ti. and semiconductor with organic and electrode with (multiple or plurality) and (adjust\$4 or vary or vari\$4 or tuning or tun\$4 or control\$4) with (capacitor or capacitance) and "361". clas.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2008/12/08 13:42
S79	201	capacitor.ab,ti. and semiconductor and organic and electrode with (multiple or plurality) and substrate and "361".clas.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2008/12/08 13:45
S80	35	capacitor.ab,ti. and semiconductor with organic and electrode with (multiple or plurality) and substrate and "361".clas.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2008/12/08 13:46
S81	518	capacitor.ab,ti. and semiconductor and electrode with (multiple or plurality) and substrate and "361".clas.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2008/12/08 14:00
S82	642	361/523.ccls.	US-PGPUB; USPAT	ADJ	ON	2009/01/08 09:26
S83	329	361/277.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2009/01/08 09:26
S84	482	361/278.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2009/01/08 09:26
S85	229	361/281.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2009/01/08 09:26

S86	85447	capacitor and electrode and semiconductor and (variable or vary or varying or varied or tune or tunable or vriable or tuning or tuned or tuning or control\$5)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2009/01/08 09:28
S87	4000	capacitor and electrode and semiconductor and (variable or vary or varying or varied or tune or tunable or vriable or tuning or tuned or tuning or control\$5) and "361". clas.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2009/01/08 09:28
S88	2093	capacitor and electrode and semiconductor and (variable or vary or varying or varied or tune or tunable or vriable or tuning or tuned or tuning or control\$5) with (capacitor or condesor or capacitance) and "361". clas.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2009/01/08 09:29
S89	976	capacitor and electrode and semiconductor and (variable or vary or varying or varied or tune or tunable or vriable or tuning or tuned or tuning or control\$5) with (capacitor or condesor or capacitance) with (volt or voltage) and "361". clas.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2009/01/08 09:30
S90	511	"361/277-300.ccls. and semiconductor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2009/01/08 09:33
S91	252	361/277-300.ccls. and semiconductor and electrode with (recess or hole or open or opening or structure or pattern or patterned or structured)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2009/01/08 09:35
S92	3	("20020074589" "20030085449" "6212056").PN. OR ("6999296").URPN.	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/01/08 09:38
S93	252	S90 not S91	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/01/08 09:41

S94	5054	(capacitor or condensor or varactor).ab.ti. and electrode and semiconductor and (variable or vary or varying or varied or tune or tunable or vriable or tuning or tuned or tuning or control\$5) with (capacitor or condensor or capacitance) with (volt or voltage)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2009/01/08 10:01
S95	2823	(capacitor or condensor or varactor).ab.ti. and electrode and substrate and semiconductor and (variable or vary or varying or varied or tune or tunable or vriable or tuning or tuned or tuning or control\$5) with (capacitor or condensor or capacitance) with (volt or voltage)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2009/01/08 10:01
S96	1521	(capacitor or condensor or varactor).ab.ti. and electrode with (recess or hole or open or opening or structure or pattern or patterned or structured) and substrate and semiconductor and (variable or vary or varying or varied or tune or tunable or vriable or tuning or tuned or tuning or control\$5) with (capacitor or condensor or capacitance) with (volt or voltage)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2009/01/08 10:02
S97	218	(capacitor or condensor or varactor).ab.ti. and electrode with (pluarity or multiple) with semiconductor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2009/01/08 11:25
S98	44	(capacitor or condensor or varactor).ab.ti. and electrode with (pluarity or multiple) with semiconductor near3 layer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2009/01/08 11:26
S99	7	(capacitor or condensor or varactor) and electrode with (pluarity or multiple) with semiconductor near3 layer and "361".clas.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2009/02/03 10:46

S100	91	(capacitor or condensor or varactor) and electrode with (structur\$4 or pattern\$4) with semiconductor near3 layer and "361".clas.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2009/02/03 10:47
S101	49	electrode with (structur\$4 or pattern\$4) and semiconductor near3 layer and 361/277-300.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2009/02/03 10:52
S102	25158	(capacitor or condensor or varactor) and electrode with (structur\$4 or pattern\$4) and semiconductor near3 layer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2009/02/03 10:57
S103	6867	(capacitor or condensor or varactor).ab.ti. and electrode with (structur\$4 or pattern\$4) and semiconductor near3 layer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2009/02/03 10:57
S104	149	((variable or varying or varied or vary or tuning or tunable or tuned or tune or trim or trimmable or trimming or trimmed or controled or controlling or controlable) with (capacitor or condensor)) or varactor).ab.ti. and electrode with (structur\$4 or pattern\$4) and semiconductor near3 layer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2009/02/03 11:23
S105	9	("3679948" "3953264" "3969750").PN. OR ("4449141").URPN.	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/02/03 11:38
S107	120	((variable or varying or varied or vary or tuning or tunable or tuned or tune or trim or trimmable or trimming or trimmed or controled or controlling or controlable) with (capacitor or condensor)) or varactor).ab.ti. and electrode with (structur\$4 or pattern\$4) and semiconductor near3 layer and (silicon or si or germanium or ge)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2009/02/11 09:30

S108	5	((variable or varying or varied or vary or tuning or tunable or tuned or tune or trim or trimmable or trimming or trimmed or controled or controlling or controlable) with (capacitor or condensor)) or varactor).ab.ti. and electrode with (structur\$4 or pattern\$4) and semiconductor near3 layer and (silicon or si or germanium or ge) with organic	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2009/02/11 09:31
S109	65	("5347144" "5355235"). PN. OR ("5705826").URPN.	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/02/11 09:34
S110	0	((variable or varying or varied or vary or tuning or tunable or tuned or tune or trim or trimmable or trimming or trimmed or controled or controlling or controlable) with (capacitor or condensor)) or varactor).ab.ti. and electrode and no with (dielctric or inulat\$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2009/02/11 10:40
S111	113	((variable or varying or varied or vary or tuning or tunable or tuned or tune or trim or trimmable or trimming or trimmed or controled or controlling or controlable) with (capacitor or condensor)) or varactor).ab.ti. and electrode and no with (dielctric or insulat\$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2009/02/11 10:43
S112	23	("3872359" "4065781" "4598305" "4782350" "4876582" "4886977" "4907041" "4916504"). PN. OR ("5038184").URPN.	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/02/11 10:50
S113	229	361/281.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2009/02/11 10:51
S114	4	((DIETMAR) near2 (ZIPPERER)).INV.	US-PGPUB; USPAT	ADJ	ON	2009/02/11 11:07
S115	43	((WOLFGANG) near2 (CLEMENS)).INV.	US-PGPUB; USPAT	ADJ	ON	2009/02/11 11:07

S116	4299	((variable or varying or varied or vary or tuning or tunable or tuned or tune or trim or trimmable or trimming or trimmed or controled or controlling or controlable) with (capacitor or condensor)) or varactor).ab.ti. and semiconductor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2009/02/11 11:08
S117	3143	((variable or varying or varied or vary or tuning or tunable or tuned or tune or trim or trimmable or trimming or trimmed or controled or controlling or controlable) with (capacitor or condensor)) or varactor).ab.ti. and semiconductor and voltage	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2009/02/11 11:08
S119	98	((variable or varying or varied or vary or tuning or tunable or tuned or tune or trim or trimmable or trimming or trimmed or controled or controlling or controlable) with (capacitor or condensor)) or varactor).ab.ti. and semiconductor and voltage and insulat\$6 with frequency	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2009/02/11 11:09
S120	467	"361".clas. and (MSM or metal near2 semiconductor near2 metal)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2009/02/11 11:17
S121	30	"361".clas. and (MSM or metal semiconductor metal)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2009/02/11 11:18
S122	582	"361".clas. and (metal or electrode) and semiconductor and voltage with (variable or varied or varing or vary or tunable or controlable or controlled or trimmable or trimmed or trimming or tuning or tuned or controlling) same capacitance	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2009/02/11 13:57

S123	338	"361".clas. and (metal or electrode) and semiconductor and voltage with (variable or varied or varing or vary or tunable or controlable or controlled or trimmable or trimmed or trimming or tuning or tuned or controlling) with capacitance	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2009/02/11 13:58
S124	4	"10219905"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2009/02/11 14:29
S125	279	((variable or varying or varied or vary or tuning or tunable or tuned or tune or trim or trimmable or trimming or trimmed or controled or controlling or controlable) with (capacitor or condensor)) or varactor).ab.ti. and "361".clas. and (plurality or multiple or structur\$4 or pattern\$5 or segment\$4) with (electrode or conductor or metal near3 layer)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2009/02/12 11:40
S126	118	((variable or varying or varied or vary or tuning or tunable or tuned or tune or trim or trimmable or trimming or trimmed or controled or controlling or controlable) with (capacitor or condensor)) or varactor).ab.ti. and "361".clas. and (plurality or multiple or structur\$4 or pattern\$5 or segment\$4) with (electrode or conductor or metal near3 layer) and semiconductor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2009/02/12 11:40

S127	464	((variable or varying or varied or vary or tuning or tunable or tuned or tune or trim or trimmable or trimming or trimmed or controled or controlling or controlable) with (capacitance)) and "361". clas. and (pluarity or multiple or structur\$4 or pattern\$5 or segment\$4) with (electrode or conductor or metal near3 layer) and semiconductor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2009/02/12 12:34
S128	312	((variable or varying or varied or vary or tuning or tunable or tuned or tune or trim or trimmable or trimming or trimmed or controled or controlling or controlable) with (capacitance)) and "361". clas. and (pluarity or multiple or structur\$4 or pattern\$5 or segment\$4) with (electrode or conductor or metal near3 layer) and semiconductor and voltage not MEMS	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2009/02/12 12:36
S129	259	((variable or varying or varied or vary or tuning or tunable or tuned or tune or trim or trimmable or trimming or trimmed or controled or controlling or controlable) with dielectric) and "361". clas. and (pluarity or multiple or structur\$4 or pattern\$5 or segment\$4) with (electrode or conductor or metal near3 layer) and semiconductor and voltage not MEMS	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2009/02/12 12:42

S130	2569	((variable or varying or varied or vary or tuning or tunable or tuned or tune or trim or trimmable or trimming or trimmed or controled or controlling or controlable) with dielectric) and ("257".clas. or "438".clas.) and (pluarity or multiple or structur\$4 or pattern\$5 or segment\$4) with (electrode or conductor or metal near3 layer) and semiconductor and voltage not MEMS	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2009/02/12 13:10
S131	2124	((variable or varying or varied or vary or tuning or tunable or tuned or tune or trim or trimmable or trimming or trimmed or controled or controlling or controlable) with (capacitance)) and ("257".clas. or "438".clas.) and (pluarity or multiple or structur\$4 or pattern\$5 or segment\$4) with (electrode or conductor or metal near3 layer) and semiconductor and voltage not MEMS	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2009/02/12 13:16
S132	2012	((variable or varying or varied or vary or tuning or tunable or tuned or tune or trim or trimmable or trimming or trimmed or controled or controlling or controlable) with (capacitance)) and ("257".clas.) and (pluarity or multiple or structur\$4 or pattern\$5 or segment\$4) with (electrode or conductor or metal near3 layer) and semiconductor and voltage not MEMS	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2009/02/12 13:18

S133	1137	((variable or varying or varied or vary or tuning or tunable or tuned or tune or trim or trimmable or trimming or trimmed or controled or controlling or controlable) with (capacitance) same voltage) and ("257".clas. or "438".clas.) and (plurality or multiple or structur\$4 or pattern\$5 or segment\$4) with (electrode or conductor or metal near3 layer) and semiconductor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2009/02/12 13:24
S134	591	((variable or varying or varied or vary or tuning or tunable or tuned or tune or trim or trimmable or trimming or trimmed or controled or controlling or controlable) with (capacitance) same voltage) and ("257".clas. or "438".clas.) and (plurality or multiple or structur\$4 or pattern\$5 or segment\$4) with (electrode or conductor or metal near3 layer) and semiconductor near3 layer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2009/02/12 13:24
S135	460	((variable or varying or varied or vary or tuning or tunable or tuned or tune or trim or trimmable or trimming or trimmed or controled or controlling or controlable) with (capacitance) same voltage) and ("257".clas. or "438".clas.) and (plurality or multiple or structur\$4 or pattern\$5 or segment\$4) with (electrode or conductor or metal near3 layer) and semiconductor near3 layer and (capacitor or varactor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2009/02/12 13:25

S136	460	((variable or varying or varied or vary or tuning or tunable or tuned or tune or trim or trimmable or trimming or trimmed or controlled or controlling or controlable) with (capacitance) same voltage) and ("257".clas. or "438".clas.) and (plurality or multiple or structur\$4 or pattern\$5 or segment\$4) with (electrode or conductor or metal near3 layer) and semiconductor near3 layer and (capacitor or varactor or condensor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2009/02/12 13:25
S137	34	(US-20070030623-\$ or US-20060098362-\$ or US-20060286737-\$ or US-20030226996-\$ or US-20030178620-\$ or US-20040223288-\$ or US-20040184216-\$ or US-20030183866-\$).did. or (US-7064345-\$ or US-5705826-\$ or US-5892244-\$ or US-6087196-\$ or US-6992322-\$ or US-7193237-\$ or US-7198977-\$ or US-5500537-\$ or US-6586791-\$ or US-6331356-\$ or US-6890792-\$ or US-6219170-\$ or US-6555840-\$ or US-5206525-\$ or US-6950299-\$ or US-6999296-\$ or US-6865066-\$ or US-4449141-\$ or US-5038184-\$ or US-6703681-\$).did. or (US-3512052-\$ or US-3508123-\$).did. or (DE-10219905-\$).did. or (JP-2001085272-\$).did. or (JP-2004320022-\$ or DE-10219905-\$).did.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2009/02/12 13:46

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